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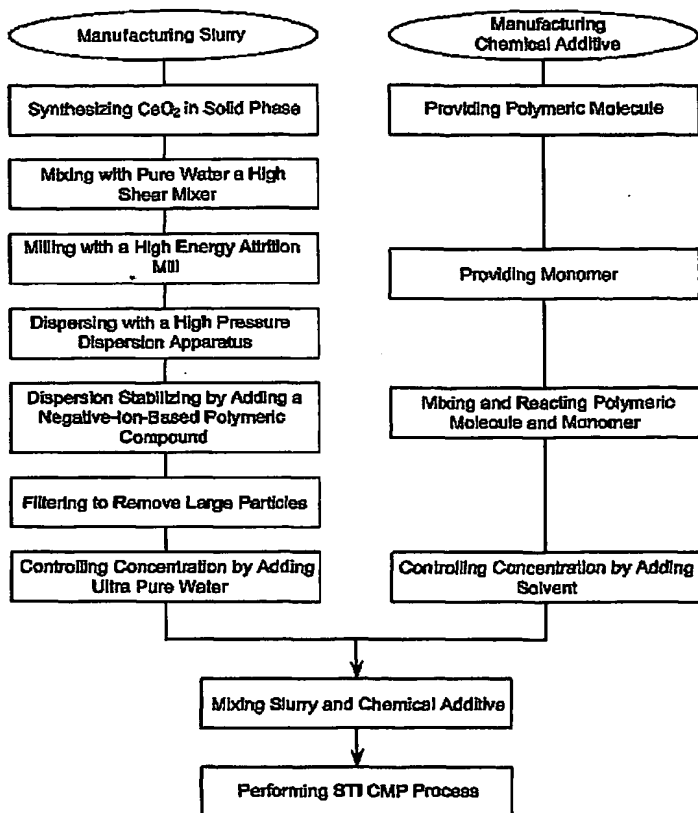
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(54) Title: CERIA ABRASIVE FOR CMP



(57) Abstract: The present invention relates to a CMP abrasive comprising a ceria slurry and a chemical additive having two or more functional groups by mixing and synthesizing a polymeric molecule and a monomer. Also, the present invention relates to a method for a manufacturing CMP abrasive by providing a ceria slurry, manufacturing a chemical additive having two or more functional groups by mixing and synthesizing of the polymeric molecule and the monomer in a reactor, and mixing said slurry and said chemical additive. Therefore, when the abrasive according to the present invention is used as an STI CMP abrasive, it is possible to apply the abrasive to the patterning process required in the very large scale integration semiconductor process. Furthermore, the CMP abrasive of the present invention has a superior removal rate, superior polishing selectivity, superior within wafer non-uniformity (WIWNU), and minimized occurrence of micro scratches.

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